

BUJ103AD

Silicon diffused power transistor

Rev. 01 — 14 December 2004

Product data sheet

1. Product profile

1.1 General description

High-voltage, high-speed planar-passivated NPN power switching transistor in a SOT428 (D-PAK) surface mounted package.

1.2 Features

- Low thermal resistance
- Fast switching

1.3 Applications

- Electronic lighting ballasts
- DC-to-DC converters
- Inverters
- Motor control systems

1.4 Quick reference data

- $V_{CESM} \leq 700 \text{ V}$
- $I_C \leq 4 \text{ A}$
- $P_{tot} \leq 80 \text{ W}$
- $h_{FEsat} = 12.5 \text{ (typ)}$

2. Pinning information

Table 1: Pinning

Pin	Description	Simplified outline	Symbol
1	base	SOT428 (D-PAK)	sym056
2	collector ^[1]		
3	emitter		
mb	mounting base; connected to collector		

[1] It is not possible to make a connection to pin 2 of the SOT428 (D-PAK) package.

3. Ordering information

Table 2: Ordering information

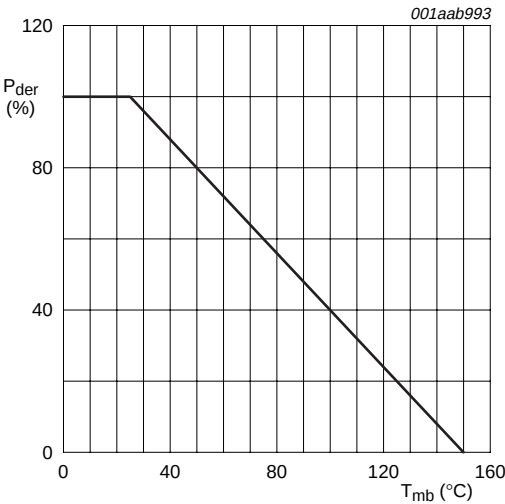
Type number	Package		
	Name	Description	Version
BUJ103AD	D-PAK	plastic single-ended surface mounted package; 3 leads (one lead cropped)	SOT428

4. Limiting values

Table 3: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CESM}	peak collector-emitter voltage	V _{BE} = 0 V	-	700	V
V _{CBO}	collector-base voltage	open emitter	-	700	V
V _{CEO}	collector-emitter voltage	open base	-	400	V
I _C	collector current (DC)		-	4	A
I _{CM}	peak collector current		-	8	A
I _B	base current (DC)		-	2	A
I _{BM}	peak base current		-	4	A
P _{tot}	total power dissipation	T _{mb} ≤ 25 °C; see Figure 1	-	80	W
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		-	150	°C



$$P_{der}(\%) = \frac{P_{tot}}{P_{tot(25\text{ °C})}} \times 100\%$$

Fig 1. Normalized total power dissipation as a function of mounting base temperature

5. Thermal characteristics

Table 4: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 2	-	-	1.56	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		^[1] -	75	-	K/W

[1] Device mounted on a printed-circuit board; minimum footprint.

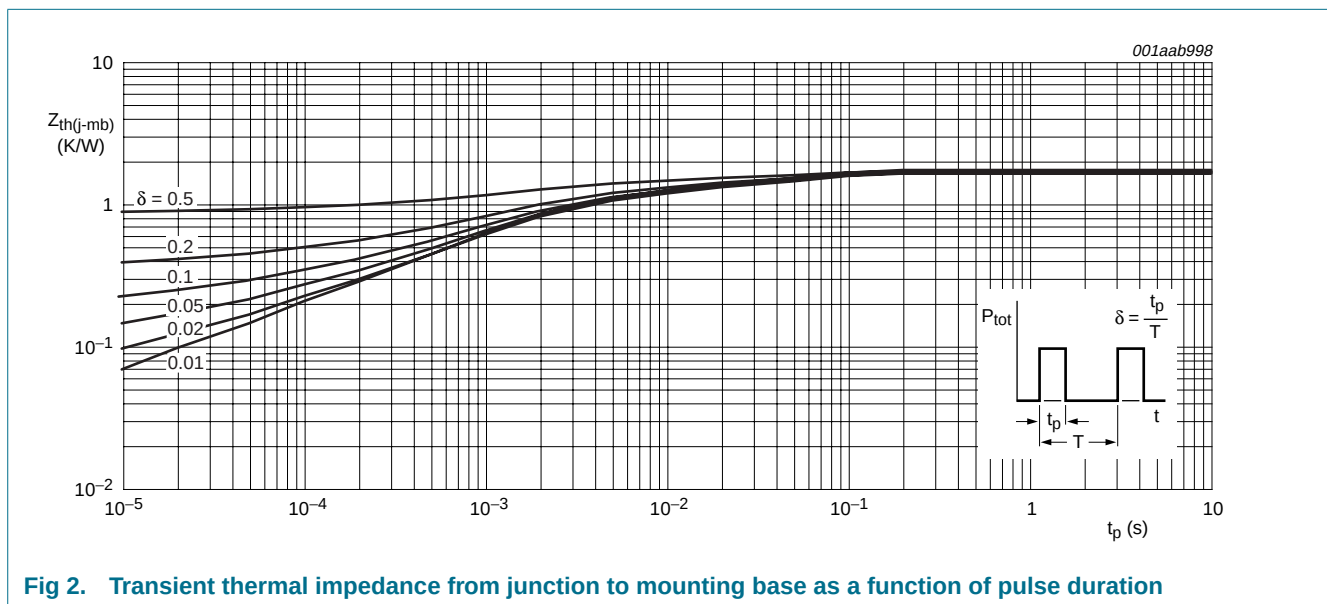


Fig 2. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 5: Characteristics

$T_{mb} = 25^\circ\text{C}$; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{CES}	collector-emitter cut-off current	$V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$	^[1] -	-	1.0	mA
		$V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}; T_j = 125^\circ\text{C}$	^[1] -	-	2.0	mA
I_{CBO}	collector-base cut-off current	$V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$	^[1] -	-	1.0	mA
I_{CEO}	collector-emitter cut-off current	$V_{CEO} = V_{CEOMmax} = 400\text{ V}$	^[1] -	-	0.1	mA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 7\text{ V}; I_C = 0\text{ A}$	-	-	0.1	mA
V_{CEOsus}	collector-emitter sustaining voltage	$I_B = 0\text{ A}; I_C = 10\text{ mA}; L = 25\text{ mH}$; see Figure 3 and 4	400	-	-	V
V_{CEsat}	collector-emitter saturation voltage	$I_C = 3.0\text{ A}; I_B = 0.6\text{ A}$; see Figure 10	-	0.25	1.0	V
V_{BEsat}	base-emitter saturation voltage	$I_C = 3.0\text{ A}; I_B = 0.6\text{ A}$; see Figure 11	-	0.97	1.5	V
h_{FE}	DC current gain	$I_C = 1\text{ mA}; V_{CE} = 5\text{ V}$; see Figure 9	10	17	32	
		$I_C = 500\text{ mA}; V_{CE} = 5\text{ V}$	13	22	32	

Table 5: Characteristics ...continued
 $T_{mb} = 25\text{ }^{\circ}\text{C}$; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
h_{FEsat}	DC saturation current gain	$I_C = 2.0\text{ A}$; $V_{CE} = 5\text{ V}$	11	16	22	
		$I_C = 3.0\text{ A}$; $V_{CE} = 5\text{ V}$	-	12.5	-	

Dynamic characteristics

Switching times (resistive load); see Figure 5 and 6

t_{on}	turn-on time	$I_{Con} = 2.5\text{ A}$; $I_{Bon} = -I_{Boff} = 0.5\text{ A}$; $R_L = 75\text{ }\Omega$	-	0.52	0.6	μs
t_{stg}	storage time		-	2.7	3.3	μs
t_f	fall time		-	0.3	0.35	μs

Switching times (inductive load); see Figure 7 and 8

t_{stg}	storage time	$I_{Con} = 2\text{ A}$; $I_{Bon} = 0.4\text{ A}$; $L_B = 1\text{ }\mu\text{H}$; $V_{BB} = -5\text{ V}$	-	1.2	1.4	μs
t_f	fall time		-	30	60	ns

Switching times (inductive load); see Figure 7 and 8

t_{stg}	storage time	$I_{Con} = 2\text{ A}$; $I_{Bon} = 0.4\text{ A}$; $L_B = 1\text{ }\mu\text{H}$; $V_{BB} = -5\text{ V}$; $T_j = 100\text{ }^{\circ}\text{C}$	-	-	1.8	μs
t_f	fall time		-	-	120	ns

[1] Measured with half sine-wave voltage (curve tracer).

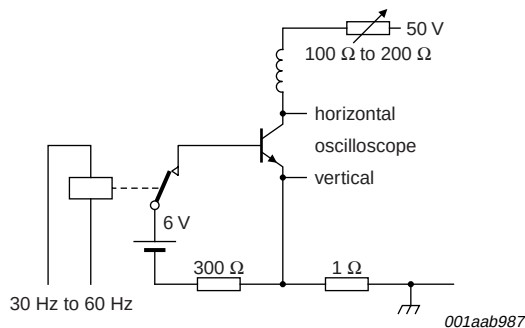


Fig 3. Test circuit for collector-emitter sustaining voltage

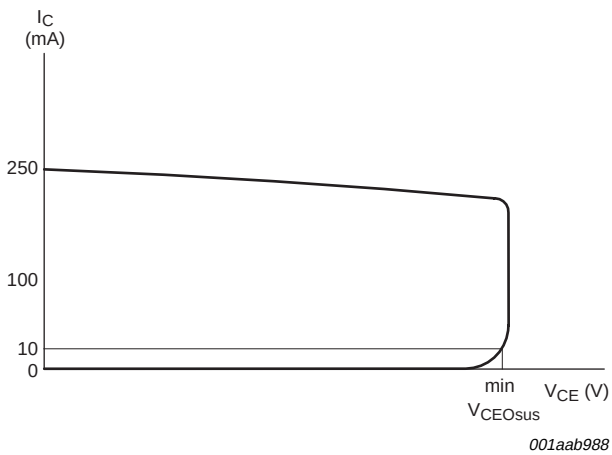
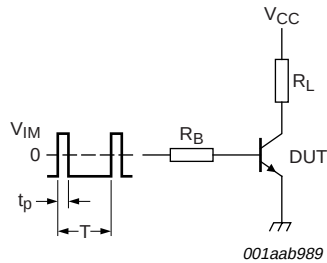


Fig 4. Oscilloscope display for collector-emitter sustaining voltage test waveform



$V_{IM} = -6 \text{ V to } +8 \text{ V}$; $V_{CC} = 250 \text{ V}$; $t_p = 20 \text{ } \mu\text{s}$;
 $\delta = t_p/T = 0.01$.
 R_B and R_L calculated from I_{Con} and I_{Bon} requirements.

Fig 5. Test circuit for resistive load switching

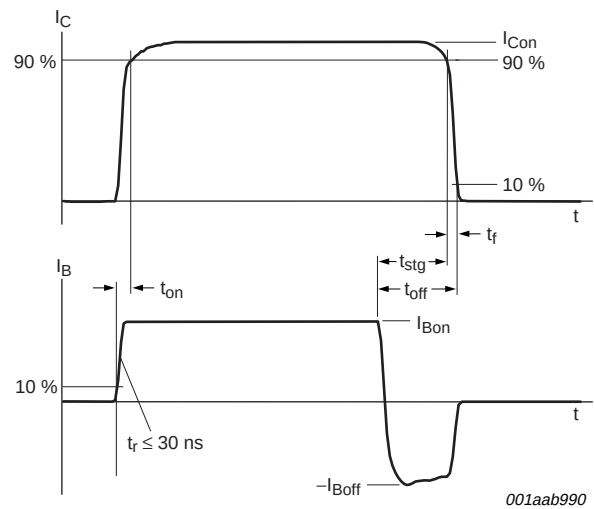
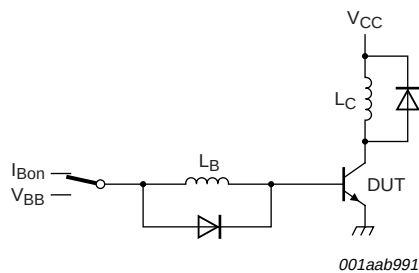


Fig 6. Switching times waveforms for resistive load



$V_{CC} = 300 \text{ V}$; $V_{BB} = -5 \text{ V}$; $L_C = 200 \text{ } \mu\text{H}$; $L_B = 1 \text{ } \mu\text{H}$.

Fig 7. Test circuit for inductive load switching

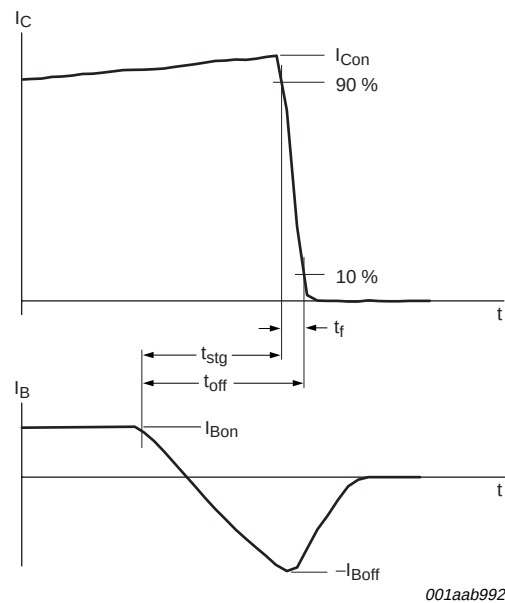


Fig 8. Switching times waveforms for inductive load

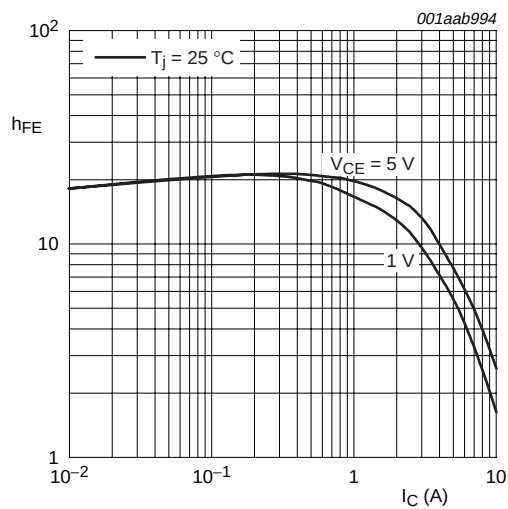
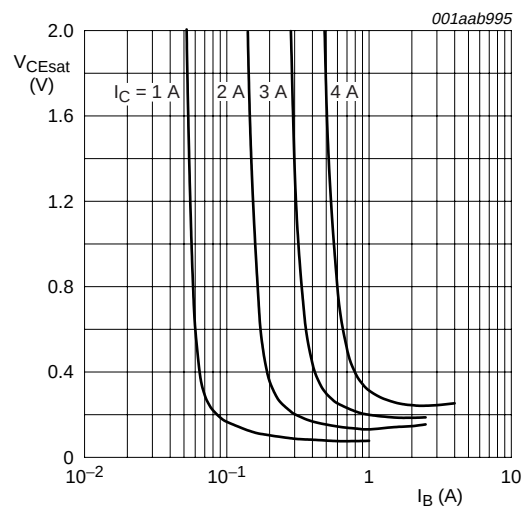
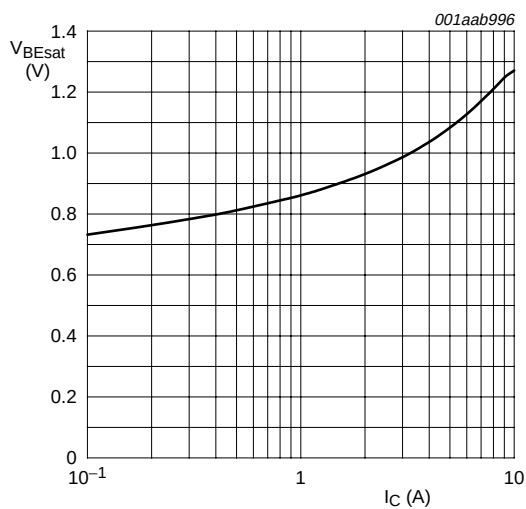


Fig 9. DC current gain as a function of collector current; typical values



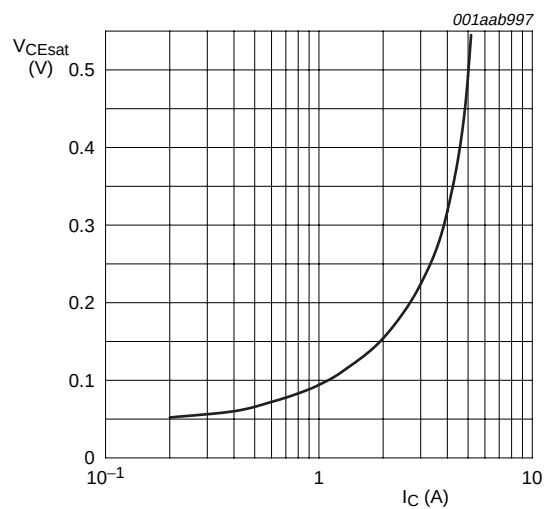
$T_j = 25\text{ }^{\circ}\text{C}$.

Fig 10. Collector-emitter saturation voltage as a function of base current; typical values



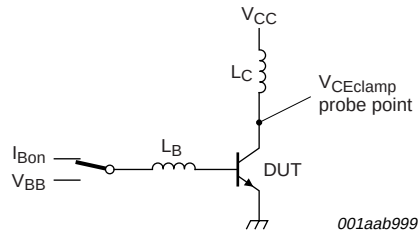
$I_C/I_B = 4$.

Fig 11. Base-emitter saturation voltage as a function of collector current; typical values



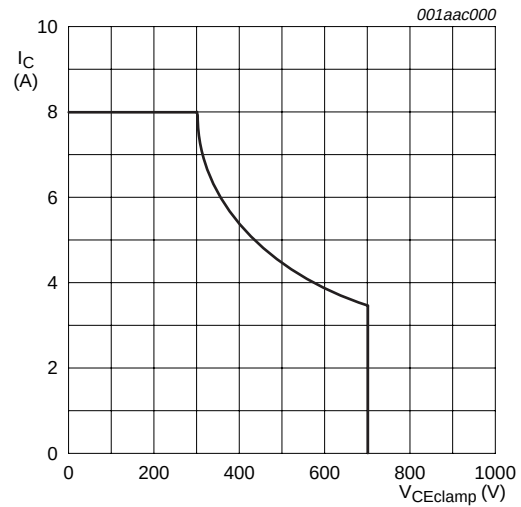
$I_C/I_B = 4$.

Fig 12. Collector-emitter saturation voltage as a function of collector current; typical values



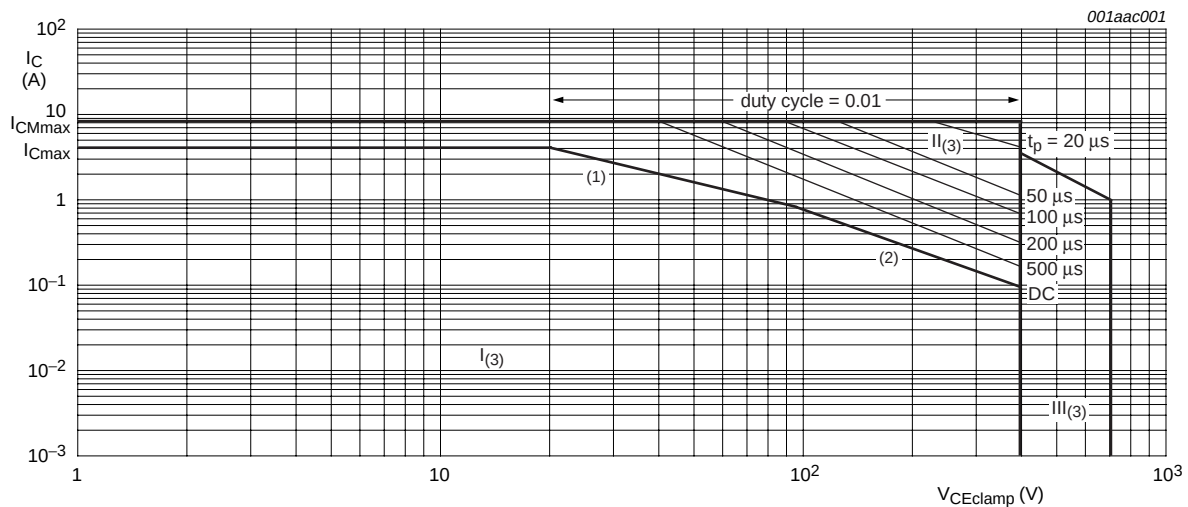
$V_{CEclamp} \leq 1000 \text{ V}$; $V_{CC} = 150 \text{ V}$; $V_{BB} = -5 \text{ V}$;
 $L_B = 1 \mu\text{H}$; $L_C = 200 \mu\text{H}$.

Fig 13. Test circuit for reverse bias safe operating area



$T_j \leq T_{j(max)}$.

Fig 14. Reverse bias safe operating area



$T_{mb} \leq 25 \text{ }^\circ\text{C}$; Mounted with heatsink compound and 30 ± 5 Newton force on the center of the envelope.

(1) P_{tot} maximum and P_{tot} peak maximum lines.

(2) Second breakdown limits.

(3) I = Region of permissible DC operation.

II = Extension for repetitive pulse operation.

III = Extension during turn-on in single transistor converters provided that $R_{BE} \leq 100 \Omega$ and $t_p \leq 0.6 \mu\text{s}$.

Fig 15. Forward bias safe operating area

7. Package information

Epoxy meets requirements of UL94 V-0 at $\frac{1}{8}$ inch.

8. Package outline

Plastic single-ended surface mounted package (D-PAK); 3 leads (one lead cropped) SOT428

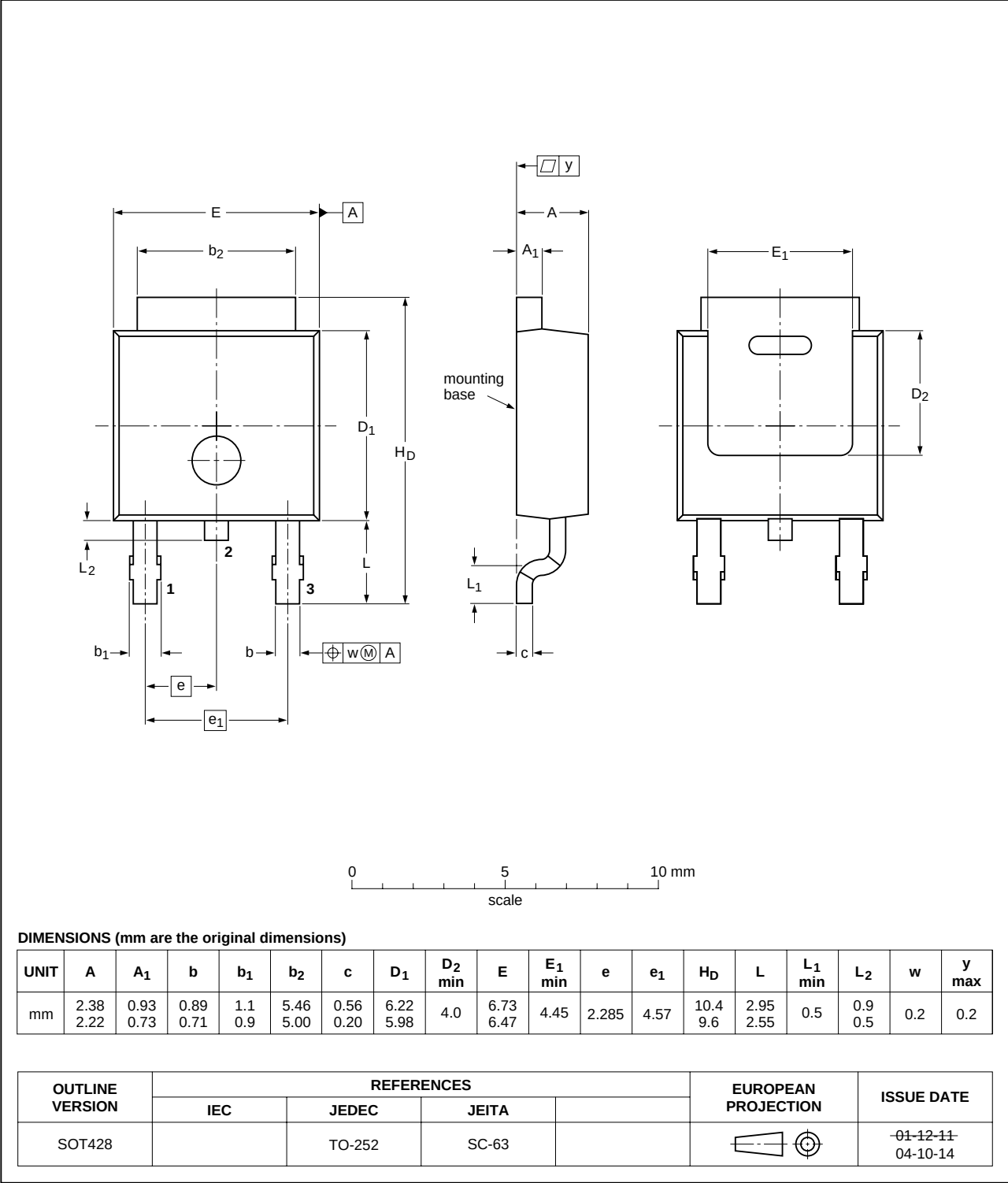
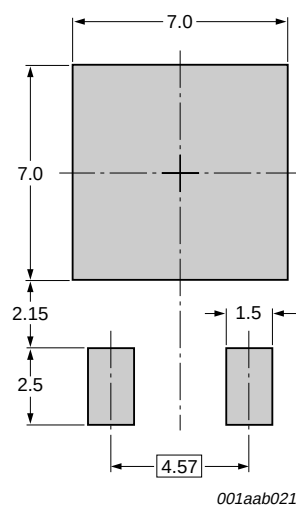


Fig 16. Package outline SOT428 (SC-63)

9. Mounting



Dimensions in mm.

Fig 17. SOT428 soldering pattern for surface mounting



10. Revision history

Table 6: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
BUJ103AD_1	20041214	Product data sheet	-	9397 750 14195	-

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Level	Data sheet status ^[1]	Product status ^{[2] [3]}	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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